

Appl. No. 10/711,392  
Amdt. dated June 12, 2005  
Reply to Office action of April 12, 2005

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

1. (Original) A chemical mechanical polishing process comprising:  
5 providing a substrate having thereon a top bulk metal layer and a lower barrier layer;  
polishing said top bulk metal layer at a substantial constant removal rate to expose  
said barrier layer by utilizing a first platen and a first slurry being selective to said barrier  
layer; and  
polishing said exposed barrier layer by using a second platen and a second slurry.  
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2. (Original) The chemical mechanical polishing process according to claim 1 wherein  
said first slurry has a copper to barrier polishing selectivity of greater than 30.
3. (Original) The chemical mechanical polishing process according to claim 2 wherein  
15 said first slurry has a copper to barrier polishing selectivity of above 100.
4. (Original) The chemical mechanical polishing process according to claim 1 wherein  
said first slurry contains alumina.
- 20 5. (Original) The chemical mechanical polishing process according to claim 1 wherein  
said second slurry contains alumina.
6. (Original) The chemical mechanical polishing process according to claim 1 wherein  
said first slurry contains silica.  
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7. (Original) The chemical mechanical polishing process according to claim 1 wherein  
said second slurry contains silica.